NPN SILICON RF POWER TRANSISTOR

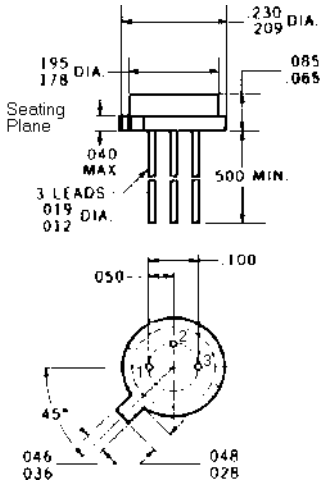
DESCRIPTION:

The **ASI MRF604** is Designed for General Purpose Oscillator Applications up to 175 MHz.

FEATURES:

- V_{CC} = 12.5 V
- P_{OUT} = 1.0 W
- ***Omnigold***™ Metalization System

PACKAGE STYLE TO-46



MAXIMUM RATINGS

I_C	150 mA
V_{CB}	40 V
P_{DISS}	2.0 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	88 °C/W

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 5.0 mA			20			V
BV_{CBO}	I_C = 100 µA			40			V
BV_{EBO}	I_E = 100 µA			3.5			V
I_{CEO}	V_{CE} = 12 V					1.0	mA
h_{FE}	V_{CE} = 5.0 V	I_C = 50 mA		20		200	---
C_{OB}	V_{CB} = 12.5 V		f = 1.0 MHz			3.5	pF
η_C	V_{CC} = 12.5 V	P_{OUT} = 1.0 W	f = 175 MHz	50			%
P_G	V_{CC} = 12.5 V	P_{OUT} = 1.0 W	f = 175 MHz	10			dB
f_t	V_{CE} = 10 V	I_E = 50 mA	f = 200 MHz	800			MHz